THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: SPENCER, GREGORY S.		§ Patent No.: 6992003 B2				
Oi t		§ Issue Date: 1/31/2006				
Application No.: 10/659885		§ Patent No.: 6992003 B2 § Issue Date: 1/31/2006 § Examiner: George A. Goudreau § Group Art Unit: 1765 § Docket No.: SC12765TP				
Filed:	09-11-2003	§ Group Art Unit: 1765				
		6 Docket No.: SC12765TP				
Title:	LOW K DIELECTRIC IN A SEMICONDUCTOR					
i ilio.	FABRICATION PROCES					
	Certificate of Submission					
I hereby certify that this correspondence is being submitted to the USPTO, Alexandria, VA.						
Addressed per C.F.R. § 1.1(a) and deposited with the United States Postal Service with sufficient postage as first class mail.						
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March 7 2008						
Date of Submission						
Teren Shephard						
Signature						
<u>leresa</u> Shephard						
Printed Name of Person Signing Certificate						
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Commissioner for Patents Alexandria, VA 22313

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed is a Certificate of Correction listing error(s) in the subject patent. Please enter these corrections. Since at least some of the errors appear to be on the part of the Applicant, the required fee may be charged to Deposit Account 503079 via the Electronic Filing System.

Respectfully submitted,

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PATENT NO.: 6992003 B2
APPLICATION NO: 10/659885
DATE: 09-11-2003

FIRST NAMED INVENTOR: SPENCER, GREGORY S.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 6, Line 20, Claim No. 1:

Change "dielectric including reducing a flaw rate" to--dielectric including reducing a flow rate--

In Column 7, Line 9, Claim No. 11:

Change "comprises an precursor selected" to--comprises a precursor selected--

In Column 7, Line 18, Claim No. 13:

Change "further wherein an radio frequency power" to--further wherein a radio frequency power--

In Column 7, Line 27, Claim No. 14:

Change "a second dielectric overlying, the first" to--a second dielectric overlying the first--

In Column 8, Line 7, Claim No. 17:

Change "wherein The organic" to--wherein the organic--

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